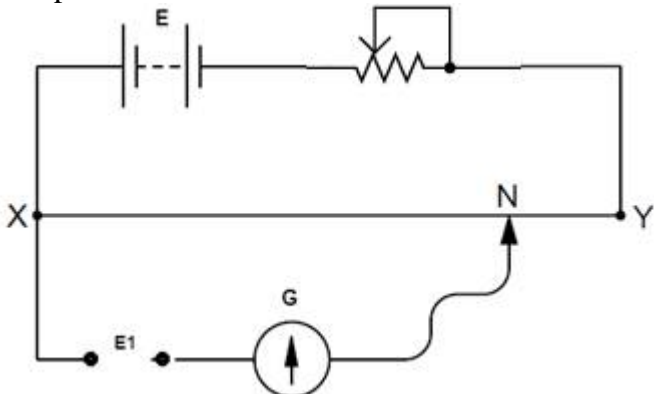
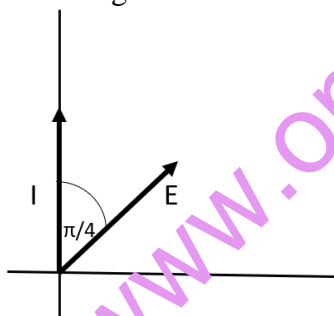


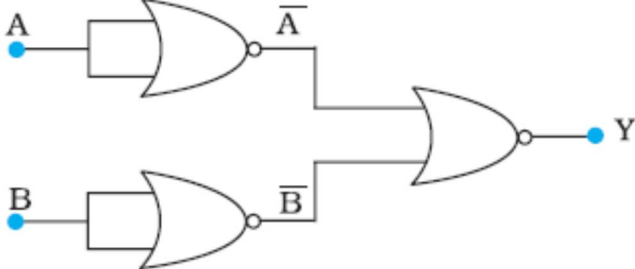
Class: XII
Physics (042)
Marking Scheme 2018-19

Time allowed: 3 hours

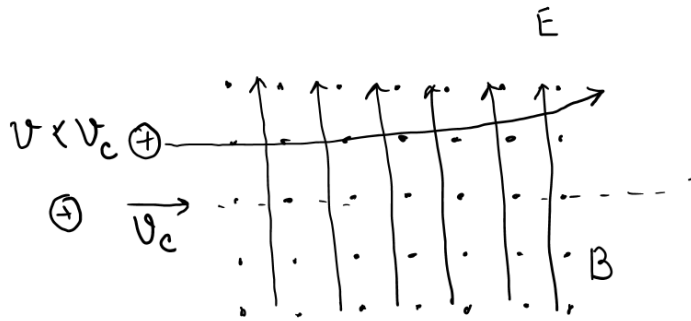
Maximum Marks: 70

[illegible]

7.	<p>The positive of E_1 is not connected to terminal X.</p>  <p>In loop PGJX, $E_1 - V_G + E_{XN} = 0$ $V_G = E_1 + E_{XN}$ $V_G = E_1 + k \ell$ So, V_G (or deflection) will be maximum when ℓ is maximum i.e. when jockey is touched near end Y. Also, V_G (or deflection) will be minimum when ℓ is minimum i.e. when jockey is touched near end X.</p> <p style="text-align: center;">OR</p>	<p>1/2</p> <p>1/2</p> <p>1/2</p>
(a)	$X = (100 - \ell) R / \ell$	1
(b)	Balancing length will increase on increase of resistance R.	1
8.	<p>Phasor diagram</p>  <p>Equal length of phasors current leads voltage phase difference is $\pi/4$</p>	<p>1/2</p> <p>1/2</p> <p>1</p>
9.	<p>(i) Radiation re-radiated by earth has greater wavelength (ii) Tanning effect is significant for direct UV radiation; it is negligible for radiation coming through the glass.</p>	<p>1</p> <p>1</p>
10.	<p>Angular width $2\Theta = 2\lambda/d$ Given $\lambda = 6000 \text{ \AA}$ In Case of new λ (assumed λ' here), angular width decreases by 30% $= \left(\frac{100-30}{100}\right) 2\Theta$ $= 0.70 (2\Theta)$</p>	<p>1/2</p> <p>1/2</p> <p>1/2</p>

	$2\lambda'/d = 0.70 \times (2\lambda/d)$ $\therefore \lambda' = 4200 \text{ \AA}$	1/2
11.	<p>Universal gates (like the NAND and the NOR gates) are gates that can be appropriately combined to realize all the three basic gates.</p> 	1
12.	<p>Range $d = \sqrt{2hR} + \sqrt{2h_R R}$ $d = 33.9 \text{ km}$</p>	1 1
SECTION: C		
13.	<p>From energy conservation, $U_i + K_i = U_f + K_f$ $kQq/r_i + 0 = kQq/r_f + K_f$ $K_f = kQq (1/r_i - 1/r_f)$</p>	1/2 1/2
	<p>When Q is $+15 \mu\text{C}$, q will move 15 cm away from it. Hence $r_f = 45 \text{ cm}$ $K_f = 9 \times 10^9 \times 15 \times 10^{-6} \times 5 \times 10^{-6} [1/(30 \times 10^{-2}) - 1/(45 \times 10^{-2})]$ $= 0.75 \text{ J}$</p>	1/2 1/2
	<p>When Q is $-15 \mu\text{C}$, q will move 15 cm towards it. Hence $r_f = 15 \text{ cm}$ $K_f = 9 \times 10^9 \times (-15 \times 10^{-6}) \times 5 \times 10^{-6} [1/(30 \times 10^{-2}) - 1/(15 \times 10^{-2})]$ $= 2.25 \text{ J}$</p>	1/2 1/2
14.	<p>(a) p_1: stable equilibrium p_2: unstable equilibrium The electric field, on either side, is directed towards the negatively charged sheet and its magnitude is independent of the distance of the field point from the sheet. For position p_1, dipole moment and electric field are parallel. For position p_2, they are antiparallel.</p>	1/2 1/2+1/2
	<p>(b) The dipole will not be in equilibrium in any of the two positions. The electric field due to an infinite straight charged wire is non-uniform ($E \propto 1/r$). Hence there will be a net non-zero force on the dipole in each case.</p>	1/2 1/2 1/2
15.	<p>(a) Drift speed in B (n-type semiconductor) is higher Reason: $I = neAv_d$ is same for both n is much lower in semiconductors.</p>	1/2 1/2
	<p>(b) Voltage drop across A will increase as the resistance of A increases with increase in temperature. Voltage drop across B will decrease as resistance of B will decrease with increase in temperature.</p>	1/2+1/2 1/2+1/2
16.	<p>$\mathbf{E} = E \mathbf{j}$ and $\mathbf{B} = B \mathbf{k}$ Force on positive ion due to electric field $\mathbf{F}_E = qE\mathbf{j}$ Force due to magnetic field $\mathbf{F}_B = q(\mathbf{v}_c \times \mathbf{B})$</p>	1/2 1/2
	<p>For passing undeflected, $\mathbf{F}_E = -\mathbf{F}_B$ $qE\mathbf{j} = -q(\mathbf{v}_c \times B\mathbf{k})$ This is possible only if $q\mathbf{v}_c \times B\mathbf{k} = qv_c B\mathbf{j}$ or $\mathbf{v}_c = (E/B)\mathbf{i}$</p>	1/2

The trajectory would be as shown.



Justification: For positive ions with speed $v < v_c$

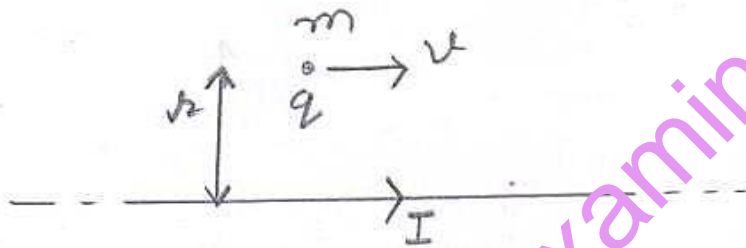
Force due to electric field $= F'_E = qE = F_E$

due to magnetic field $F'_B = qvB < F_B$ since $v < v_c$

Now forces are unbalanced, and hence, ion will experience an acceleration along **E**.

Since initial velocity is perpendicular to **E**, the trajectory would be parabolic.

OR



For the charged particle to move undeflected

Net force $\vec{F} = \vec{F}_E + \vec{F}_m = 0$

$$\vec{F}_E = -\vec{F}_m \quad (1)$$

$\vec{F}_E \rightarrow$ electric force, $\vec{F}_m \rightarrow$ magnetic force

$$|\vec{F}_E| = |\vec{F}_m| \quad (2)$$

$$qE = Bqv \sin 90^\circ = Bqv$$

$$E = vB \quad (3)$$

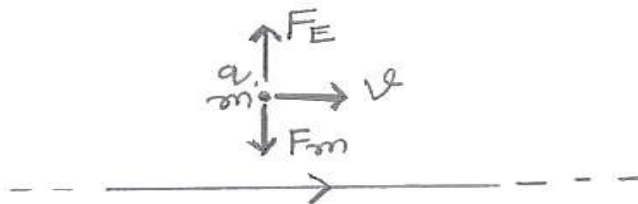
$$B = \frac{\mu_0 I}{2\pi r} \quad (4)$$

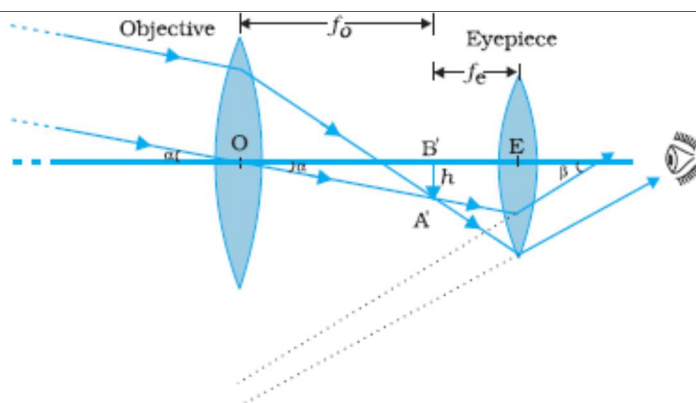
Using (4) and (3)

$$E = \frac{\mu_0 I v}{2\pi r} \quad (5)$$

Magnetic force F_m is towards wire.

\therefore Electric force and electric field should be away from the line.





Drawbacks:

(i) Large sized lenses are heavy and difficult to support

(ii) large sized lenses suffer from chromatic and spherical aberration.

1/2

1/2

OR

(a) Resolving power of a telescope is the reciprocal of the smallest angular separation between the two objects which can be just distinctly seen.

Factors: diameter of the objective, wavelength of the incident light

1

1/2+1/2

(b) a telescope produces image of far objects nearer to our eye. Objects which are not resolved at far distance, can be resolved by telescope. A microscope, on the other hand magnifies objects nearer to us and produces their large image.

1

20. Let d be the diameter of the disc. The spot shall be invisible if the incident rays from the dot at O , at the center of the disc, are incident at the critical angle of incidence. Let i be the critical angle of incidence.

$$\text{Then } \sin i = \frac{1}{\mu}$$

$$\text{Now, } \frac{d/2}{h} = \tan i$$

$$\Rightarrow \frac{d}{2} = h \tan i = h \left[\sqrt{\mu^2 - 1} \right]^{-1}$$

$$\therefore d = \frac{2h}{\sqrt{\mu^2 - 1}}$$

1

1/2

1/2

1/2

1/2

21. (a) No, it is not necessary that if the energy supplied to an electron is more than the work function, it will come out. The electron after receiving energy, may lose energy to the metal due to collisions with the atoms of the metal. Therefore, most electrons get scattered into the metal. Only a few electrons near the surface may come out of the surface of the metal for whom the incident energy is greater than the work function of the metal.

1

1

(b) on reducing the distance, intensity increases.

Photoelectric current increases with the increase in intensity.

Stopping potential is independent of intensity, and therefore remains unchanged.

1/2

1/2

22. Energy corresponding to the given wavelength:

$$E \text{ (in eV)} = \frac{12400}{\lambda \text{ (in \AA)}} = 12.71 \text{ eV}$$

The excited state:

$$E_n - E_1 = 12.71$$

$$\frac{-13.6}{n^2} + 13.6 = 12.71$$

$$\therefore n = 3.9 \approx 4$$

$$\text{Total no. of spectral lines emitted: } \frac{n(n-1)}{2} = 6$$

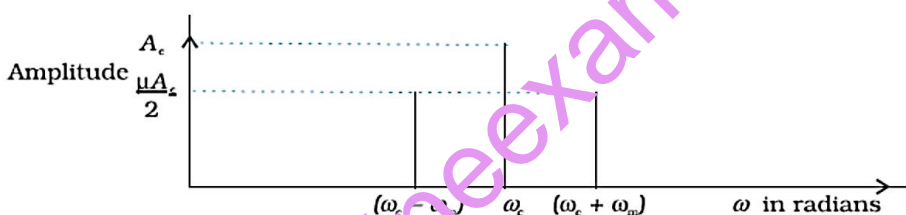
Longest wavelength will correspond to the transition

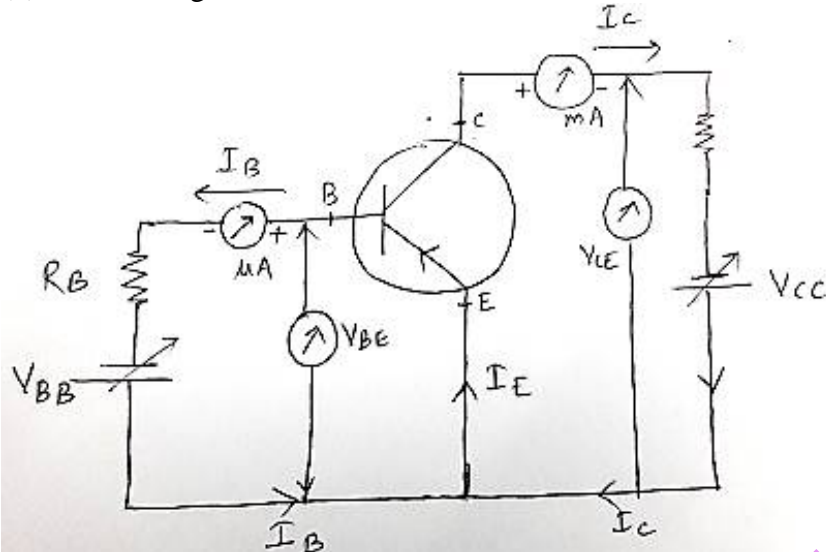
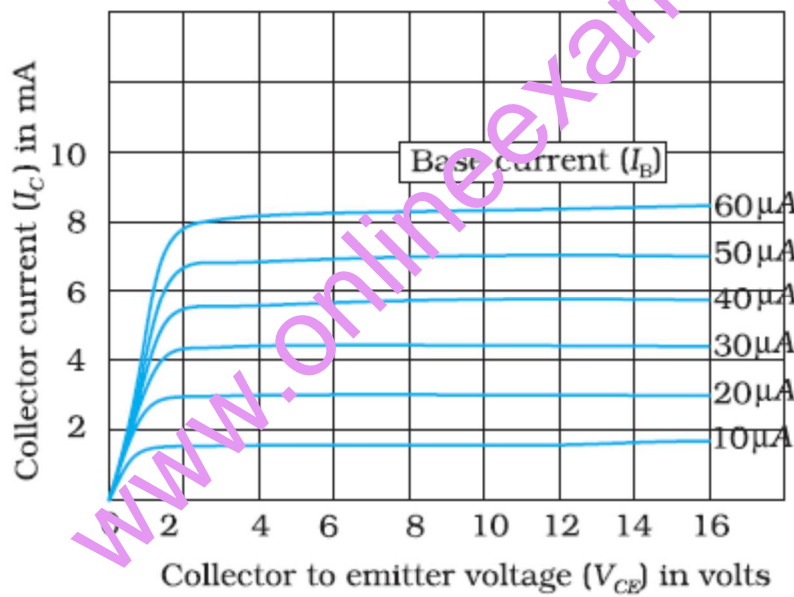
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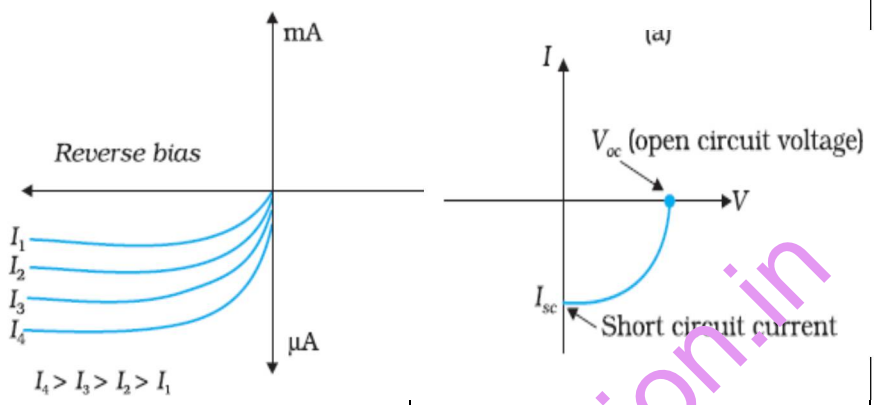
1/2

1/2

1/2

	$n = 4$ to $n = 3$	1/2
23.	(a) S, W, X	1
	(b) $Z = Z_1 + Z_2$ $A = A_1 + A_2$	1/2 1/2
	(c) Reason for low binding energy:- In heavier nuclei, the Coulombian repulsive effects can increase considerably and can match/ offset the attractive effects of the nuclear forces. This can result in such nuclei being unstable.	1
	OR	
	Nuclear force binds the protons inside the nucleus. For Graph and explanation, refer to NCERT page no 445 Significance of negative potential energy: Force is attractive in nature	1/2 2 1/2
24.	The modulated signal: $C_m(t) = (A_c + A_m \sin \omega_m t) \sin \omega_c t$ $= A_c \left(1 + \frac{A_m}{A_c} \sin \omega_m t \right) \sin \omega_c t$ $C_m(t) = A_c \sin \omega_c t + \mu A_c \sin \omega_m t \sin \omega_c t$ $C_m(t) = A_c \sin \omega_c t + \frac{\mu A_c}{2} \cos(\omega_c - \omega_m) t - \frac{\mu A_c}{2} \cos(\omega_c + \omega_m) t$ Frequency Spectrum :- 	1/2 1/2 1/2 1/2 1
	SECTION: D	
25.	(a) The equivalent magnetic moment is given by $\mu = NiA$ The direction of μ is perpendicular to the plane of current carrying loop. It is directed along the direction of advance of a right-handed screw rotated along the direction of flow of current derivation of expression for μ of electron revolving around a nucleus	1/2 1/2 2
	(b) for the loop, $\mu = N (\pi r^2) i (\pm \mathbf{k})$ Magnetic potential energy = $\mu \cdot \mathbf{B}$ $= N (\pi r^2) i (\pm \mathbf{k}) \cdot (B_x \mathbf{i} + B_y \mathbf{j} + B_z \mathbf{k})$ $= \pm \pi r^2 N I B_z$	1/2 1/2 1/2 1/2
	OR	
	(a) Derivation $H = nI$ The direction of \mathbf{H} is along the axis of the solenoid, directed along the direction of advance of a right-handed screw rotated along the direction of flow of current	2.5 1/2
	(b) (i) Not necessarily. Reason: material is diamagnetic. After removal of magnetising field, no magnetisation will remain in the material and hence earth's magnetic field	1/2 1/2

	Refracted light: Partially polarised	1/2
27.	<p>(a) Circuit diagram</p> 	2
	<p>(b) output characteristics is the variation of collector current with collector -emitter voltage for different fixed value of I_B. If V_{BE} is increased by a small amount, both the hole current and electron current in the base region increases. As a result, both I_B and I_C increases proportionately.</p>  <p>Output resistance is the ratio of change in collector-emitter voltage to the change in collector current.</p> <p>Current amplification factor is ratio of change in collector current to the change in base current at constant collector- emitter voltage.</p>	1
	OR	
	(a) The fractional change in majority charge carriers is very less compared to the fractional change in minority charge carriers on illumination.	1
	(b) The difference in the working of two devices:	

	Photodiode	Solar cell
Biasing	Used in Reverse biasing (½)	No external biasing is given (½)
Junction Area	Small (½)	Large for solar radiation to be incident on it. (½)
I-V characteristics	 <p>(1)</p>	
